Darlington Power Transistors

DPAK For Surface Mount Applications

Designed for general purpose power and switching such as output or driver stages in applications such as switching regulators, convertors, and power amplifiers.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Monolithic Construction With Built-in Base-Emitter Shunt Resistors
- High DC Current Gain $h_{FE} = 2500$ (Typ) @ $I_C = 4.0$ Adc
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings:
 - Human Body Model, 3B > 8000 V
 - Machine Model, C > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CB}	80	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current Continuous Peak	I _C	4 8	Adc
Base Current	Ι _Β	100	mAdc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 These ratings are applicable when surface mounted on the minimum pad sizes recommended.



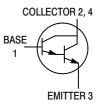
ON Semiconductor®

http://onsemi.com

SILICON POWER TRANSISTORS 4 AMPERES, 80 VOLTS, 20 WATTS



DPAK CASE 369C STYLE 1



MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week J6039 = Device Code G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MJD6039T4	DPAK	2,500/Tape & Reel
MJD6039T4G	DPAK (Pb-Free)	2,500/Tape & Reel
NJVMJD6039T4G	DPAK (Pb-Free)	2,500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage $(I_C = 30 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	80	-	Vdc
Collector–Cutoff Current $(V_{CE} = 40 \text{ Vdc}, I_B = 0)$	I _{CEO}	-	10	μAdc
ON CHARACTERISTICS (Note 3)	•			
DC Current Gain $(I_C = 1 \text{ Adc, } V_{CE} = 4 \text{ Vdc})$ $(I_C = 2 \text{ Adc, } V_{CE} = 4 \text{ Vdc})$	h _{FE}	1000 500	- -	-
Collector–Emitter Saturation Voltage (I _C = 2 Adc, I _B = 8 mAdc)	V _{CE(sat)}	-	2.5	Vdc
Base-Emitter On Voltage (I _C = 2 Adc, V _{CE} = 4 Vdc)	V _{BE(on)}	-	2.8	Vdc
DYNAMIC CHARACTERISTICS				
Small-Signal Current Gain (I _C = 0.75 Adc, V _{CE} = 10 Vdc, f = 1 kHz)	h _{fe}	25	-	_
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)	C _{ob}	-	100	pF

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

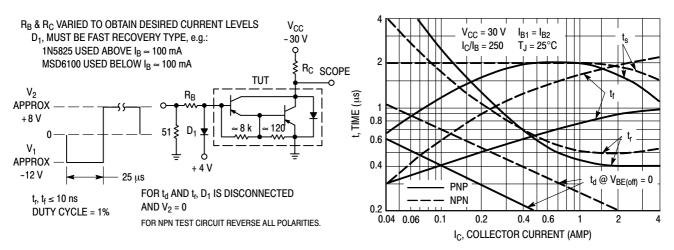


Figure 1. Switching Times Test Circuit

Figure 2. Switching Times

TYPICAL ELECTRICAL CHARACTERISTICS

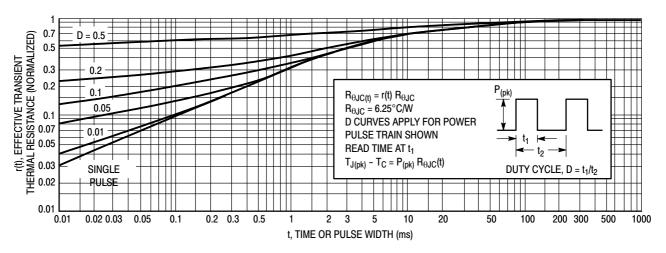


Figure 3. Thermal Response

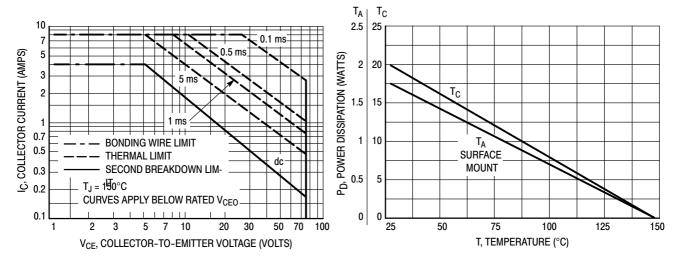


Figure 4. Maximum Rated Forward Biased Safe Operating Area

Figure 5. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 6 and 7 is based on $T_{J(pk)}=150^{\circ} C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)}$ < $150^{\circ} C$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

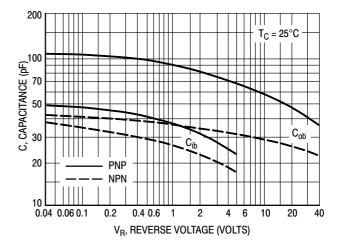


Figure 6. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

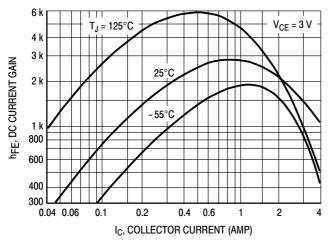


Figure 7. DC Current Gain

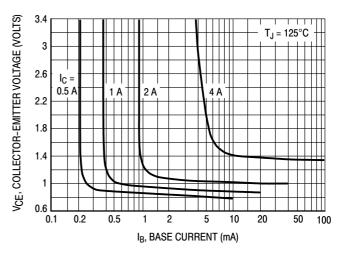


Figure 8. Collector Saturation Region

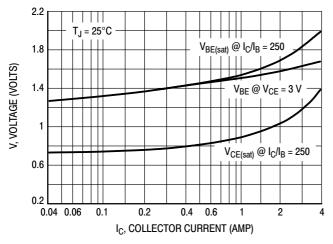


Figure 9. "On" Voltages

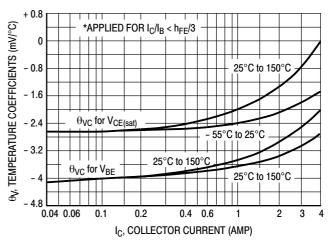


Figure 10. Temperature Coefficients

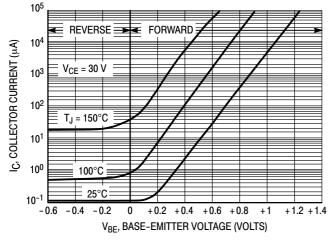


Figure 11. Collector Cut-Off Region

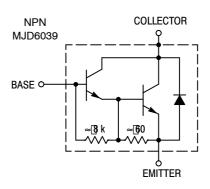
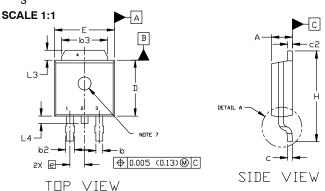


Figure 12. Darlington Schematic





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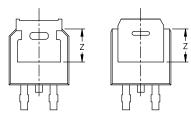


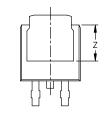
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. L3, AND Z.

 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 DIMENSIONS D AND E ARE DETERMINED AT THE
 OUTERMOST EXTREMES OF THE PLASTIC BODY.
 DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
 DETININAL MOLD ESCALUPE.

- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIM	ETERS
MIM	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
C	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

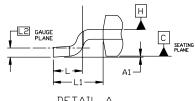




BOTTOM VIEW

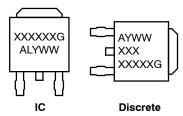
BOTTOM VIEW ALTERNATE CONSTRUCTIONS

5.80 [0.228] 6.20 [0.244] 2.58 3.00 [0.102] [0.118] 1.60 [0.063] 6.17 [0.243]



DETAIL A ROTATED 90° CW

GENERIC MARKING DIAGRAM*



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

*This information is generic. Please refer to

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

3 FMITTER

4. COLLECTOR

s

3 GATE

RECOMMENDED MOUNTING FOOTPRINT*

STYLE 1: STYLE 2: PIN 1. BASE PIN 1. GATE 2. COLLECTOR 2. DRAIL 3. EMITTER 3. SOUF 4. COLLECTOR 4. DRAIL	N 2. CATHODE RCE 3. ANODE	3. GATE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
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STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 6: STYLE 8: STYLE 9: STYLE 10: PIN 1. MT1 2. MT2 PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE

4. CATHODE

device data sheet for actual part marking. PIN 1. CATHODE 2. ANODE 3. CATHODE Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may 3 RESISTOR ADJUST not follow the Generic Marking. 4. ANODE

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

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